A Low Power / Low Latency 10G AFE In CMOS

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Low Power, 380mW / CH



Cha	nnel	Pow	<i>i</i> er

Transmitter	130mW	
Receiver Line-up	120mW	
Analog FIR	100mW	
PLL	30mW	
	200m\\\	
	3801114	
X 4 =	1.52W	
VCO and Others	140mW	
Total (4 Channels)	1.66W	

(1.56G baud Mode)





1.56GBaud Mode



Captured Waveforms



4PAM Eye Pattern, 1.56G Baud



Key Elements of A High Performance AFE

- Highly Linear Line Driver / Hybrid
- Analog Pre-Echo Canceller (Adaptive FIR) Pre-Processing, Low Noise Floor
- Fine Resolution Comparator / ADC
- Low Jitter Oscillator



Measured Results: Line Driver With 48dB of Linearity



Measured Results:

Analog Pre-Echo Canceller (Adaptive FIR)



0.2

A/D Requirement

Noise Floor 130~-140dBm/Hz

2mV Comparator Resolution

(V)

200

400

600

800

1000

Frequency, MHz

1200

1400

1600

1800

2000

-135

-140

Measured Results: Oscillator Jitter



Temp. Coef = 0.008ps/deg

Measured from -5 to 85 degC



Jitter < 3ps from –5 to 85 deg.C

Jitter Requirement from previously presented papers 4ps (Broadcom, Vativ, Marvel) 3ps (NEC Electronics) 6ps (SolarFlare)

Measured Results: Reach Performance

			Patch Panel tor 4RJ scenario
Error	Full Duplex	35m	
Reach	Simplex	50m	Cables for 2RJ scenario



833MBaud Mode

Summary

- Highly Liner (48dB) Line Driver
- 38dB Cancellation by Analog Pre-Echo Canceller
- Fine Resolution Comparator / ADC
- Less than 3ps Jitter from –5 to 85degC
- Power Consumption: 380mW / Channel
- Latency: 5ns(AFE Core) and 55ns including Scrambler / De-Scrambler and SYS-INF.
- A Low Power / Low Latency AFE at 833M up to 1.6G baud has been proven in silicon

